

SOT-23 Formed SMD Package

CSC2712

SILICON PLANAR EPITAXIAL TRANSISTOR

N-P-N transistor

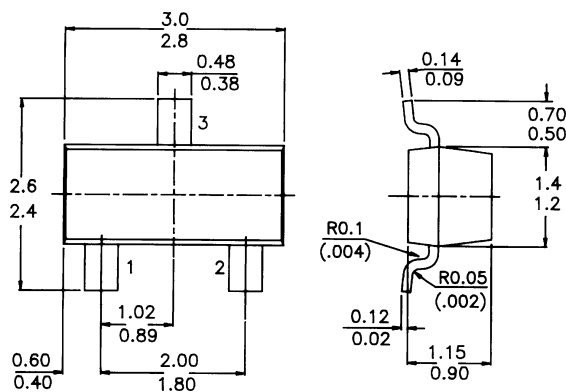
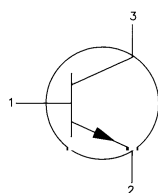
Marking

CSC2712Y=1E
CSC2712GR(G)=1F
CSC2712BL(L)=1G

PACKAGE OUTLINE DETAILS ALL DIMENSIONS IN mm

Pin configuration

1 = BASE
2 = EMITTER
3 = COLLECTOR



ABSOLUTE MAXIMUM RATINGS

Collector-base voltage (open emitter)
Collector-emitter voltage (open base)
Emitter-base voltage (open collector)
Collector current (peak value)
Total power dissipation at $T_{amb} = 25^{\circ}C$
Junction temperature
D.C. current gain
 $-I_C = 2 \text{ mA}; -V_{CE} = 6V$

V_{CBO}	max.	60 V
V_{CEO}	max.	50 V
V_{EBO}	max.	5 V
I_C	max.	150 mA
P_{tot}	max.	150 mW
T_j	max.	150 °C
h_{FE}	min.	70
	max.	700

Transition frequency

$I_C = 1 \text{ mA}; V_{CE} = 10 \text{ V}$

Noise figure at $R_S = 10 \text{ K}\Omega$

$I_C = 0.1 \text{ mA}; V_{CE} = 6V;$

$f = 1 \text{ kHz}$

f_T	min.	80 MHz
F	max	10 dB

RATINGS (at $T_A = 25^\circ\text{C}$ unless otherwise specified)*Limiting values*

Collector-base voltage (open emitter)	V_{CBO}	max.	60 V
Collector-emitter voltage (open base)	V_{CEO}	max.	50 V
Emitter-base voltage (open collector)	V_{EBO}	max.	5 V
Collector current (d.c.)	I_C	max.	150 mA
Base current	I_B	max.	30 mA
Total power dissipation at $T_{amb} = 25^\circ\text{C}$	P_{tot}	max.	150 mW
Junction temperature	T_j	max.	150 °C
Storage temperature	T_{stg}	-50 to +150	°C

CHARACTERISTICS (at $T_A = 25^\circ\text{C}$ unless otherwise specified)*Collector cut-off current*

$I_E = 0; V_{CB} = 60 \text{ V}$	I_{CBO}	max.	100 nA
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Emitter cut-off current

$I_C = 0; V_{EB} = 5 \text{ V}$	I_{EBO}	max.	100 nA
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Saturation voltage

$I_C = 100 \text{ mA}; I_B = 10 \text{ mA}$	V_{CEsat}	max.	250 mV
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D.C. current gain

$I_C = 2 \text{ mA}; V_{CE} = 6 \text{ V}$	h_{FE}	min.	70
		max.	700
	Y	min.	120
		max.	240
	$GR(G)$	min.	200
		max.	400
	$BL(L)$	min.	350
		max.	700

Transition frequency

$I_C = 1 \text{ mA}; V_{CE} = 10 \text{ V}$	f_T	min.	80 MHz
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Noise figure at $R_g = 10 \text{ k}\Omega$

$V_{CE} = 6 \text{ V}; I_C = 0.1 \text{ mA}$	N_F	max.	10 dB
$f = 1 \text{ kHz}$			

Disclaimer

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Continental Device India Limited

C-120 Naraina Industrial Area, New Delhi 110 028, India.
Telephone + 91-11-579 6150 Fax + 91-11-579 9569, 579 5290
e-mail sales@cdil.com www.cdil.com